

AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A compound semiconductor substrate for epitaxial growth, wherein when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of a substrate, by intensity of the incident light from the light source, the light source having a wavelength of 488 nm,

the haze is not more than 2 ppm all over an effectively used area of the substrate and an off-angle with respect to a plane direction is 0.05 to 0.10°, wherein the effectively used area includes the surface area of the substrate, with the exception of the peripheral part including the chamfered part of the substrate.

2. (Original) The compound semiconductor substrate as claimed in claim 1, wherein the haze is not more than 1 ppm all over the effectively used area of the substrate.

3. (Original) The compound semiconductor substrate as claimed in claim 1 or 2, wherein the compound semiconductor substrate is an InP substrate.

4. (Original) The compound semiconductor substrate as claimed in claim 3, wherein a dislocation density is not more than 1000/cm².

5. (Original) The compound semiconductor substrate as claimed in claim 4, wherein the dislocation density is not more than 500/cm².